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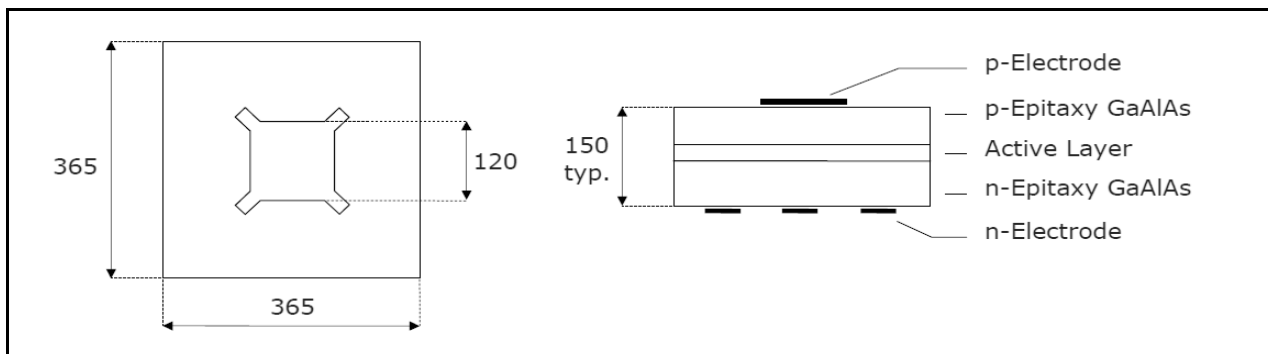
Data Sheet

LED Chip Infrared

EOLC-890-17

Rev. 02, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, substrate removed	P (anode) up



Wire bond contact can also be square

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.3	1.6	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	2.8	3.5		mW
Radiant power*	$I_F = 50 \text{ mA}$	Φ_e	7	8.5		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	880	890	900	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		55		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		80; 100		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 112



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.